



TO-92 Plastic-Encapsulate Transistors

STA124 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_D: 0.625 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

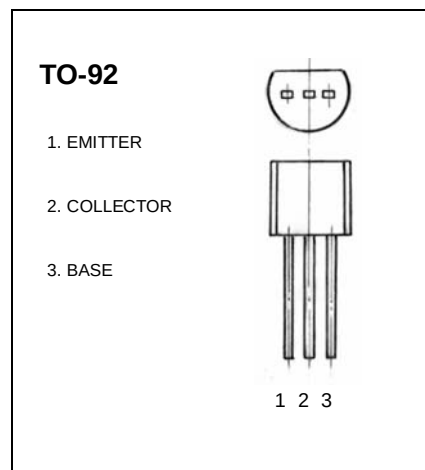
$$I_{CM}: -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -15 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-6.5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -15\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	200		450	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.2	-0.4	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -50\text{mA}$		120		MHz
Output capacitance	C_{ob}	$V_{CE} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		5		pF